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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re the Application of: **IRINO, Kiyoshi**

Group Art Unit: 2815

Serial No.: 09/428,052

Examiner: Jose R. Diaz

Filed: **October 27, 1999**

P.T.O. Confirmation No.: 4139

For: **METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (As Amended)**

RESPONSE UNDER 37 CFR §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2815

BOX AF

Commissioner for Patents
Washington, D.C. 20231

November 14, 2002

Sir:

In response to the Office Action dated **August 14, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 10 as follows:

10. (Six Times Amended) A method of fabricating a semiconductor device, comprising the steps of:
- forming a gate oxide film on a substrate by a thermal oxide film;
 - forming a gate electrode pattern on said gate oxide film such that said gate electrode pattern

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